**2SJ420**

P-Channel Silicon MOSFET

Ultrahigh-Speed

Switching Applications

Features

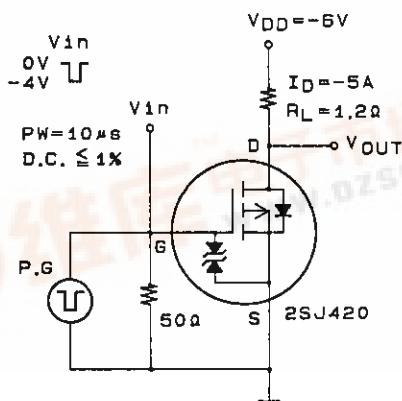
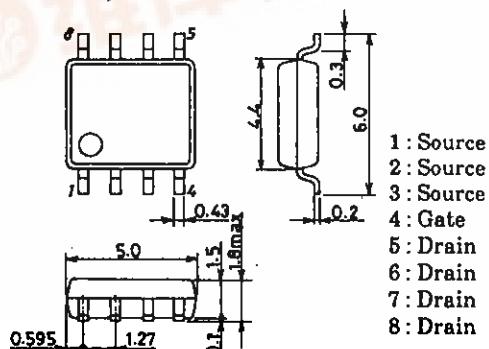
- Low ON resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Absolute Maximum Ratings at Ta=25°C

			unit
Drain-to-Source Voltage	V _{DSS}	-12	V
Gate-to-Source Voltage	V _{GSS}	±10	V
Drain Current (DC)	I _D	-5	A
Drain Current (Pulse)	I _{DP}	-32	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (1000mm ² ×0.8mm)	2.0 W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

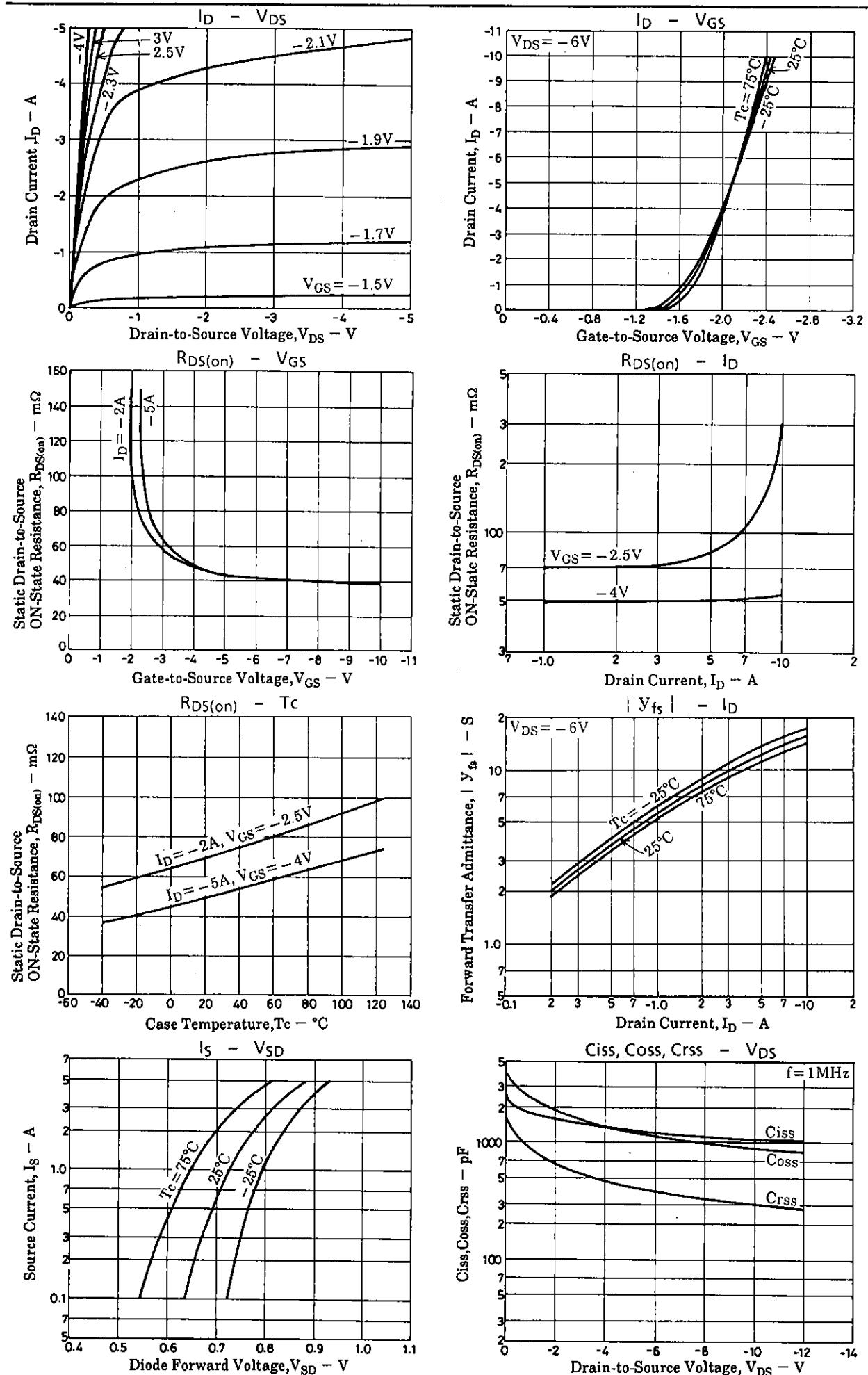
Electrical Characteristics at Ta=25°C

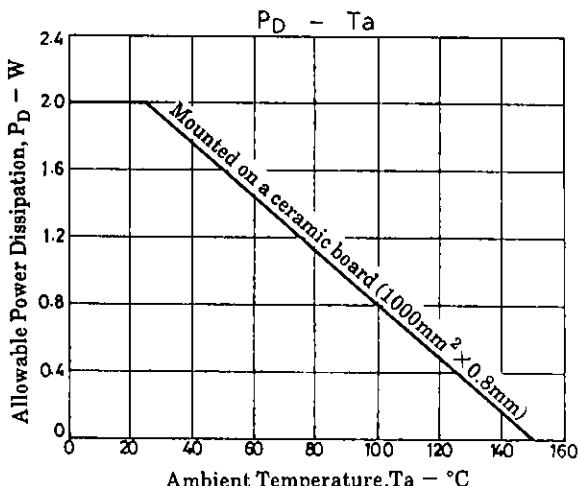
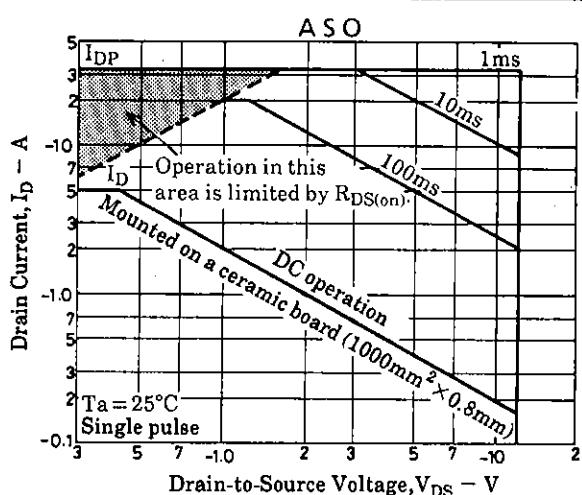
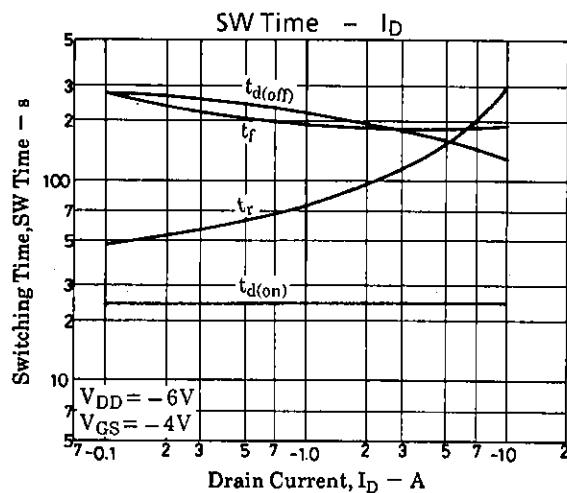
			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D =-1mA, V _{GS} =0	-12			V
Zero-Gate Voltage	I _{DSS}	V _{DS} =-10V, V _{GS} =0			-100	μA
Drain Current						
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-6V, I _D =-1mA	-0.4		-1.4	V
Forward Transfer Admittance	Y _{fs}	V _{DS} =-6V, I _D =-5A	8	12		S
Static Drain-to-Source	R _{D(on)1}	I _D =-5A, V _{GS} =-4V	50	63		mΩ
ON-State Resistance	R _{D(on)2}	I _D =-2A, V _{GS} =-2.5V	70	108		mΩ
Input Capacitance	C _{iss}	V _{DS} =-6V, f=1MHz	1200			pF
Output Capacitance	C _{oss}	V _{DS} =-6V, f=1MHz	1100			pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =-6V, f=1MHz	400			pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.	25			ns
Rise Time	t _r	"	150			ns
Turn-OFF Delay Time	t _{d(off)}	"	150			ns
Fall Time	t _f	"	180			ns
Diode Forward Voltage	V _{SD}	I _S =-5A, V _{GS} =0	-1.0	-1.2		V

Switching Time Test Circuit**Package Dimensions 2116**
(unit : mm)

SANYO:SOP8

2SJ420





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